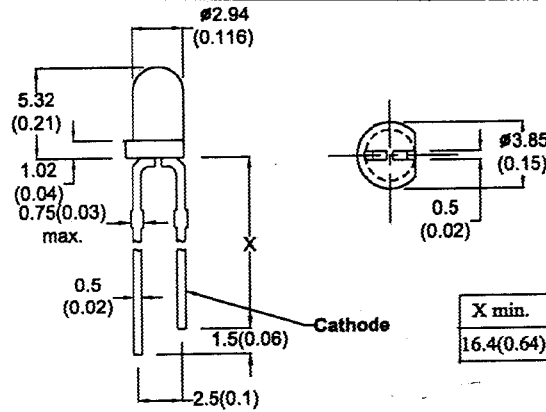


MICRO ELECTRONICS

MI32TA
 INFRARED
 EMITTING
 DIODE

DESCRIPTION

MI32TA is GaAlAs infrared emitting diode molded in 3mm diameter clear transparent lens.



- All dimension in mm (inch)
- No Scale
- Tol. : +/- 0.3mm

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	180mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po		2.8		mW	IF=20mA
Forward Voltage	VF			1.8	V	IF=20mA
Reverse Current	IR			100	μA	VR=5V
Half Intensity Beam Angle	θHI		35		degree	IF=20mA
Peak Wavelength	λp		880		nm	IF=20mA
Spectrum Line Half Width	Δλ		70		nm	IF=20mA



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MI32TA

